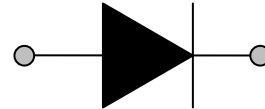
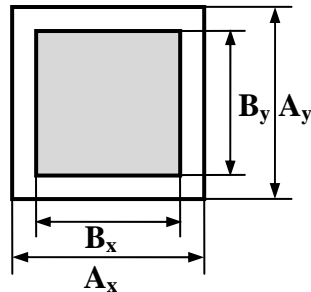


Rev.1. March 2010.

SM-3,3

Chip TVS diode.



Mechanical date: $A_x=A_y=450\mu\text{m}$
 $B_x=B_y=310\mu\text{m}$

Schematic and pinning diagram.

Chip thickness: $230\pm 20\mu\text{m}$

Scribe Line width - $60\mu\text{m}$.

Top Metal-Cathode: Al metallization for wire bond

Back side - Anode: Ti-Ni-Ag for soldering.

Limiting values

Parameter	Symbol	Conditions	Value	Unit
Reverse Stand-off voltage	V_{RWM}	-	3.3	V
Peak Pulse Power	P_{pp}	$t_p=8/20\mu\text{s}$	250*	W
Peak Pulse Current	I_{pp}	$t_p=8/20\mu\text{s}$	16,0*	A
Max.junction temperature	T_j	-	+125	°C

Characteristics ($T_j=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{BR}	Breakdown voltage	$I_R=1\text{mA}$	5,2	5,7	6,2	V
I_R	Reverse leakage current	$V_R=3,3\text{V}$	-	-	5,0	μA
C_j	Diode capacitance	$F=1\text{MHz}$, $V_{dc}=0\text{V}$	-	175	220	pF
V_{CL}	Clamping Voltage	$I_{pp}=1\text{A}$, $t_p=8/20\mu\text{s}$ $I_{pp}=5\text{A}$, $t_p=8/20\mu\text{s}$ $I_{pp}=16\text{A}$, $t_p=8/20\mu\text{s}$	-	-	6,7* 8,2* 15,6*	V
V_f	Forward voltage	$I_F=10\text{mA}$	-	0,75	-	V

*- For Device testing